

74HC00-Q100; 74HCT00-Q100

Quad 2-input NAND gate

Rev. 1 — 12 July 2012

Product data sheet

1. General description

The 74HC00-Q100; 74HCT00-Q100 are high-speed Si-gate CMOS devices that comply with JEDEC standard no. 7A. They are pin compatible with Low-power Schottky TTL (LSTTL).

The 74HC00-Q100; 74HCT00-Q100 provides a quad 2-input NAND function.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$
- Input levels:
 - ◆ For 74HC00-Q100: CMOS level
 - ◆ For 74HCT00-Q100: TTL level
- ESD protection:
 - ◆ MIL-STD-883, method 3015 exceeds 2000 V
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V ($C = 200\text{ pf}$, $R = 0\text{ }\Omega$)
- Multiple package options



3. Ordering information

Table 1. Ordering information

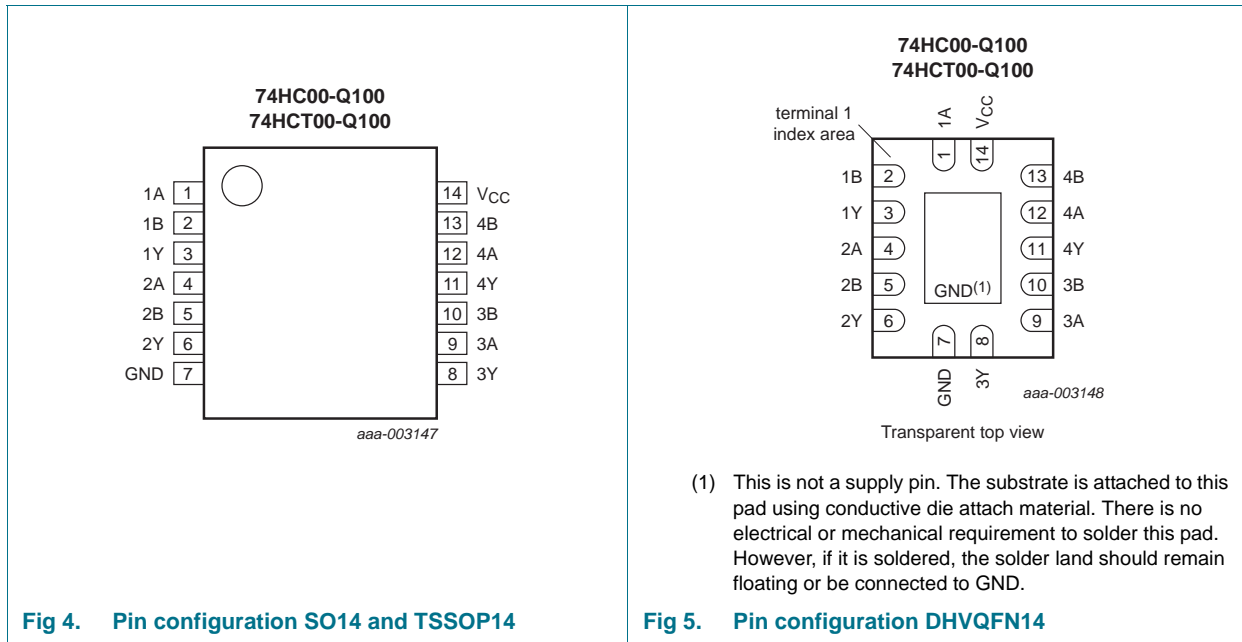
| Type number | Package | | | Version |
|---------------------------------|-------------------|----------|--|----------|
| | Temperature range | Name | Description | |
| 74HC00D-Q100 74HCT00D-Q100 | -40 °C to +125 °C | SO14 | plastic small outline package; 14 leads; body width 3.9 mm | SOT108-1 |
| 74HC00PW-Q100 74HCT00PW-Q100 | -40 °C to +125 °C | TSSOP14 | plastic thin shrink small outline package; 14 leads; body width 4.4 mm | SOT402-1 |
| 74HC00BQ-Q100 74HCT00BQ-Q100 | -40 °C to +125 °C | DHVQFN14 | plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 × 3 × 0.85 mm | SOT762-1 |

4. Functional diagram

| | | |
|----------------------------|--------------------------------|--|
| <p><i>mna212</i></p> | <p><i>mna246</i></p> | <p><i>mna211</i></p> |
| Fig 1. Logic symbol | Fig 2. IEC logic symbol | Fig 3. Logic diagram (one gate) |

5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

| Symbol | Pin | Description |
|-----------------|--------------|----------------|
| 1A to 4A | 1, 4, 9, 12 | data input |
| 1B to 4B | 2, 5, 10, 13 | data input |
| 1Y to 4Y | 3, 6, 8, 11 | data output |
| GND | 7 | ground (0 V) |
| V _{cc} | 14 | supply voltage |

6. Functional description

Table 3. Function table^[1]

| Input | | Output |
|-------|----|--------|
| nA | nB | nY |
| L | X | H |
| X | L | H |
| H | H | L |

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|-----------|-------------------------|--|-------|----------|------|
| V_{CC} | supply voltage | | -0.5 | +7 | V |
| I_{IK} | input clamping current | $V_I < -0.5\text{ V}$ or $V_I > V_{CC} + 0.5\text{ V}$ | [1] - | ± 20 | mA |
| I_{OK} | output clamping current | $V_O < -0.5\text{ V}$ or $V_O > V_{CC} + 0.5\text{ V}$ | [1] - | ± 20 | mA |
| I_O | output current | $-0.5\text{ V} < V_O < V_{CC} + 0.5\text{ V}$ | - | ± 25 | mA |
| I_{CC} | supply current | | - | 50 | mA |
| I_{GND} | ground current | | -50 | - | mA |
| T_{stg} | storage temperature | | -65 | +150 | °C |
| P_{tot} | total power dissipation | | [2] - | 500 | mW |

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SO14 package: P_{tot} derates linearly with 8 mW/K above 70 °C.
 For TSSOP14 packages: P_{tot} derates linearly with 5.5 mW/K above 60 °C.
 For DHVQFN14 packages: P_{tot} derates linearly with 4.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

| Symbol | Parameter | Conditions | 74HC00-Q100 | | | 74HCT00-Q100 | | | Unit |
|---------------------|-------------------------------------|-------------------------|-------------|------|----------|--------------|------|----------|------|
| | | | Min | Typ | Max | Min | Typ | Max | |
| V_{CC} | supply voltage | | 2.0 | 5.0 | 6.0 | 4.5 | 5.0 | 5.5 | V |
| V_I | input voltage | | 0 | - | V_{CC} | 0 | - | V_{CC} | V |
| V_O | output voltage | | 0 | - | V_{CC} | 0 | - | V_{CC} | V |
| T_{amb} | ambient temperature | | -40 | +25 | +125 | -40 | +25 | +125 | °C |
| $\Delta t/\Delta V$ | input transition rise and fall rate | $V_{CC} = 2.0\text{ V}$ | - | - | 625 | - | - | - | ns/V |
| | | $V_{CC} = 4.5\text{ V}$ | - | 1.67 | 139 | - | 1.67 | 139 | ns/V |
| | | $V_{CC} = 6.0\text{ V}$ | - | - | 83 | - | - | - | ns/V |

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | 25 °C | | | -40 °C to +85 °C | | -40 °C to +125 °C | | Unit |
|--------------------|---------------------------|---|-------|------|-----|------------------|------|-------------------|------|------|
| | | | Min | Typ | Max | Min | Max | Min | Max | |
| 74HC00-Q100 | | | | | | | | | | |
| V _{IH} | HIGH-level input voltage | V _{CC} = 2.0 V | - | 1.2 | - | 1.5 | - | 1.5 | - | V |
| | | V _{CC} = 4.5 V | - | 2.4 | - | 3.15 | - | 3.15 | - | V |
| | | V _{CC} = 6.0 V | - | 3.2 | - | 4.2 | - | 4.2 | - | V |
| V _{IL} | LOW-level input voltage | V _{CC} = 2.0 V | - | 0.8 | - | - | 0.5 | - | 0.5 | V |
| | | V _{CC} = 4.5 V | - | 2.1 | - | - | 1.35 | - | 1.35 | V |
| | | V _{CC} = 6.0 V | - | 2.8 | - | - | 1.8 | - | 1.8 | V |
| V _{OH} | HIGH-level output voltage | V _I = V _{IH} or V _{IL} | | | | | | | | |
| | | I _O = -20 μA; V _{CC} = 2.0 V | - | 2.0 | - | 1.9 | - | 1.9 | - | V |
| | | I _O = -20 μA; V _{CC} = 4.5 V | - | 4.5 | - | 4.4 | - | 4.4 | - | V |
| | | I _O = -20 μA; V _{CC} = 6.0 V | - | 6.0 | - | 5.9 | - | 5.9 | - | V |
| | | I _O = -4.0 mA; V _{CC} = 4.5 V | - | 4.32 | - | 3.84 | - | 3.7 | - | V |
| | | I _O = -5.2 mA; V _{CC} = 6.0 V | - | 5.81 | - | 5.34 | - | 5.2 | - | V |
| V _{OL} | LOW-level output voltage | V _I = V _{IH} or V _{IL} | | | | | | | | |
| | | I _O = 20 μA; V _{CC} = 2.0 V | - | 0 | - | - | 0.1 | - | 0.1 | V |
| | | I _O = 20 μA; V _{CC} = 4.5 V | - | 0 | - | - | 0.1 | - | 0.1 | V |
| | | I _O = 20 μA; V _{CC} = 6.0 V | - | 0 | - | - | 0.1 | - | 0.1 | V |
| | | I _O = 4.0 mA; V _{CC} = 4.5 V | - | 0.15 | - | - | 0.33 | - | 0.4 | V |
| | | I _O = 5.2 mA; V _{CC} = 6.0 V | - | 0.16 | - | - | 0.33 | - | 0.4 | V |
| I _I | input leakage current | V _I = V _{CC} or GND; V _{CC} = 6.0 V | - | - | - | - | ±1 | - | ±1 | μA |
| I _{CC} | supply current | V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V | - | - | - | - | 20 | - | 40 | μA |
| C _I | input capacitance | | - | 3.5 | - | - | - | - | - | pF |

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | 25 °C | | | -40 °C to +85 °C | | -40 °C to +125 °C | | Unit |
|---------------------|---------------------------|---|-------|------|-----|------------------|------|-------------------|-----|------|
| | | | Min | Typ | Max | Min | Max | Min | Max | |
| 74HCT00-Q100 | | | | | | | | | | |
| V _{IH} | HIGH-level input voltage | V _{CC} = 4.5 V to 5.5 V | - | 1.6 | - | 2.0 | - | 2.0 | - | V |
| V _{IL} | LOW-level input voltage | V _{CC} = 4.5 V to 5.5 V | - | 1.2 | - | - | 0.8 | - | 0.8 | V |
| V _{OH} | HIGH-level output voltage | V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V | - | 4.5 | - | 4.4 | - | 4.4 | - | V |
| | | I _O = -20 μA | - | 4.5 | - | 4.4 | - | 4.4 | - | V |
| | | I _O = -4.0 mA | - | 4.32 | - | 3.84 | - | 3.7 | - | V |
| V _{OL} | LOW-level output voltage | V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V | - | 0 | - | - | 0.1 | - | 0.1 | V |
| | | I _O = 20 μA; V _{CC} = 4.5 V | - | 0 | - | - | 0.1 | - | 0.1 | V |
| | | I _O = 5.2 mA; V _{CC} = 6.0 V | - | 0.15 | - | - | 0.33 | - | 0.4 | V |
| I _I | input leakage current | V _I = V _{CC} or GND; V _{CC} = 6.0 V | - | - | - | - | ±1 | - | ±1 | μA |
| I _{CC} | supply current | V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V | - | - | - | - | 20 | - | 40 | μA |
| ΔI _{CC} | additional supply current | per input pin; V _I = V _{CC} - 2.1 V; I _O = 0 A; other inputs at V _{CC} or GND; V _{CC} = 4.5 V to 5.5 V | - | 150 | - | - | 675 | - | 735 | μA |
| C _I | input capacitance | | - | 3.5 | - | - | - | - | - | pF |

10. Dynamic characteristics

Table 7. Dynamic characteristicsGND = 0 V; C_L = 50 pF; for load circuit see [Figure 7](#).

| Symbol | Parameter | Conditions | 25 °C | | | -40 °C to +125 °C | | Unit | |
|--------------------|-------------------------------|--|-------|-----|-----|-------------------|--------------|------|----|
| | | | Min | Typ | Max | Max (85 °C) | Max (125 °C) | | |
| 74HC00-Q100 | | | | | | | | | |
| t _{pd} | propagation delay | nA, nB to nY; see Figure 6 | | [1] | | | | | |
| | | V _{CC} = 2.0 V | - | 25 | - | 115 | 135 | ns | |
| | | V _{CC} = 4.5 V | - | 9 | - | 23 | 27 | ns | |
| | | V _{CC} = 5.0 V; C _L = 15 pF | - | 7 | - | - | - | ns | |
| | | V _{CC} = 6.0 V | - | 7 | - | 20 | 23 | ns | |
| t _t | transition time | see Figure 6 | | [2] | | | | | |
| | | V _{CC} = 2.0 V | - | 19 | - | 95 | 110 | ns | |
| | | V _{CC} = 4.5 V | - | 7 | - | 19 | 22 | ns | |
| | | V _{CC} = 6.0 V | - | 6 | - | 16 | 19 | ns | |
| C _{PD} | power dissipation capacitance | per package; V _I = GND to V _{CC} | | [3] | - | 22 | - | - | pF |

Table 7. Dynamic characteristics ...continued
GND = 0 V; C_L = 50 pF; for load circuit see Figure 7.

| Symbol | Parameter | Conditions | 25 °C | | | -40 °C to +125 °C | | Unit | |
|---------------------|-------------------------------|--|-------|-----|-----|-------------------|--------------|------|----|
| | | | Min | Typ | Max | Max (85 °C) | Max (125 °C) | | |
| 74HCT00-Q100 | | | | | | | | | |
| t _{pd} | propagation delay | nA, nB to nY; see Figure 6 | [1] | | | | | | |
| | | V _{CC} = 4.5 V | - | 12 | - | 24 | 29 | ns | |
| | | V _{CC} = 5.0 V; C _L = 15 pF | - | 10 | - | - | - | ns | |
| t _t | transition time | V _{CC} = 4.5 V; see Figure 6 | [2] | - | - | - | 29 | 22 | ns |
| C _{PD} | power dissipation capacitance | per package; V _I = GND to V _{CC} - 1.5 V | [3] | - | 22 | - | - | - | pF |

- [1] t_{pd} is the same as t_{PHL} and t_{PLH}.
- [2] t_t is the same as t_{THL} and t_{TLH}.
- [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW):
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$ where:
 f_i = input frequency in MHz;
 f_o = output frequency in MHz;
 C_L = output load capacitance in pF;
 V_{CC} = supply voltage in V;
 N = number of inputs switching;
 ∑ (C_L × V_{CC}² × f_o) = sum of outputs.

11. Waveforms

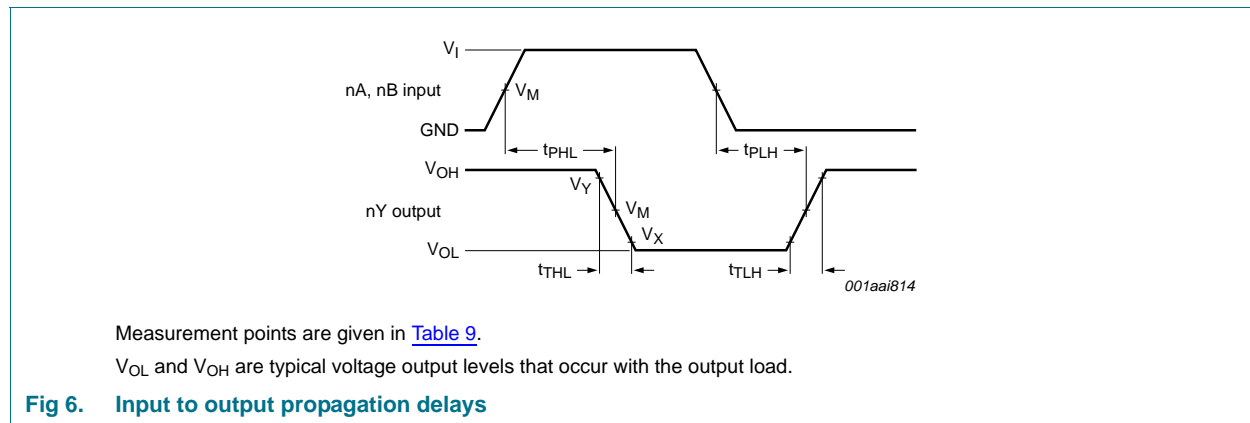


Table 8. Measurement points

| Type | Input | Output | | |
|--------------|--------------------|--------------------|--------------------|--------------------|
| | V _M | V _M | V _X | V _Y |
| 74HC00-Q100 | 0.5V _{CC} | 0.5V _{CC} | 0.1V _{CC} | 0.9V _{CC} |
| 74HCT00-Q100 | 1.3 V | 1.3 V | 0.1V _{CC} | 0.9V _{CC} |

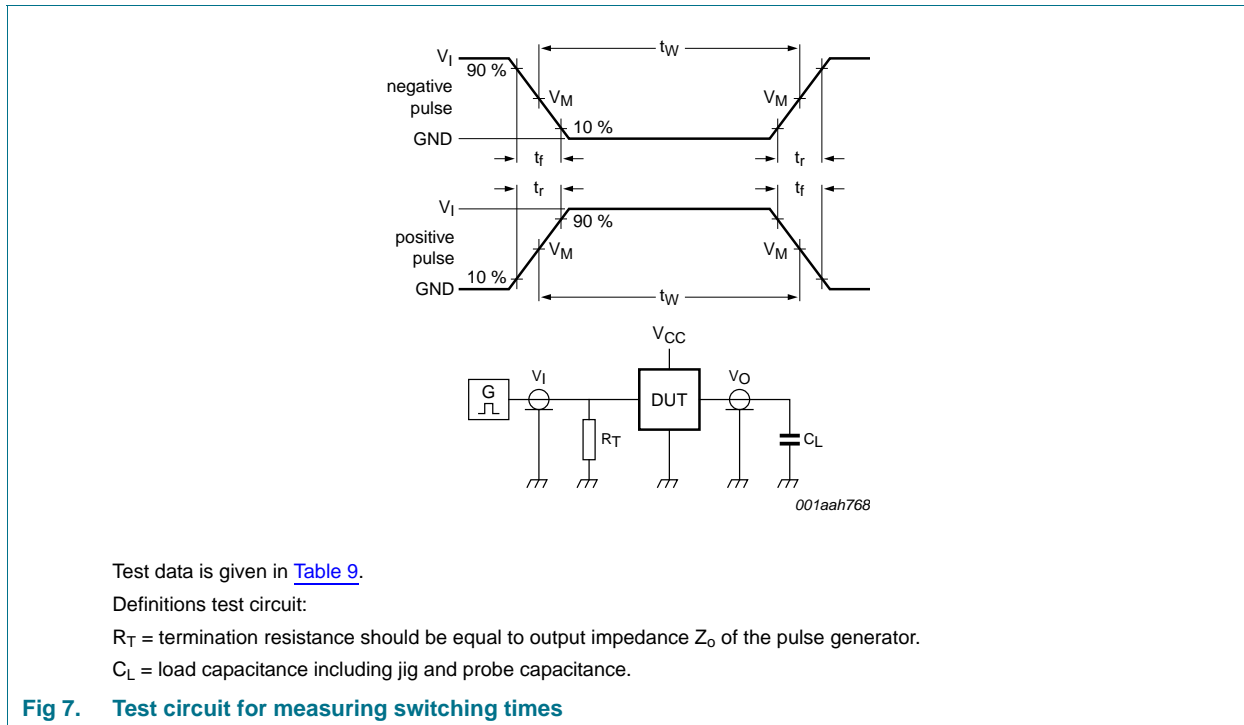


Table 9. Test data

| Type | Input | | Load | Test |
|--------------|----------|------------|--------------|--------------------|
| | V_I | t_r, t_f | C_L | |
| 74HC00-Q100 | V_{CC} | 6.0 ns | 15 pF, 50 pF | t_{PLH}, t_{PHL} |
| 74HCT00-Q100 | 3.0 V | 6.0 ns | 15 pF, 50 pF | t_{PLH}, t_{PHL} |

12. Package outline

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1

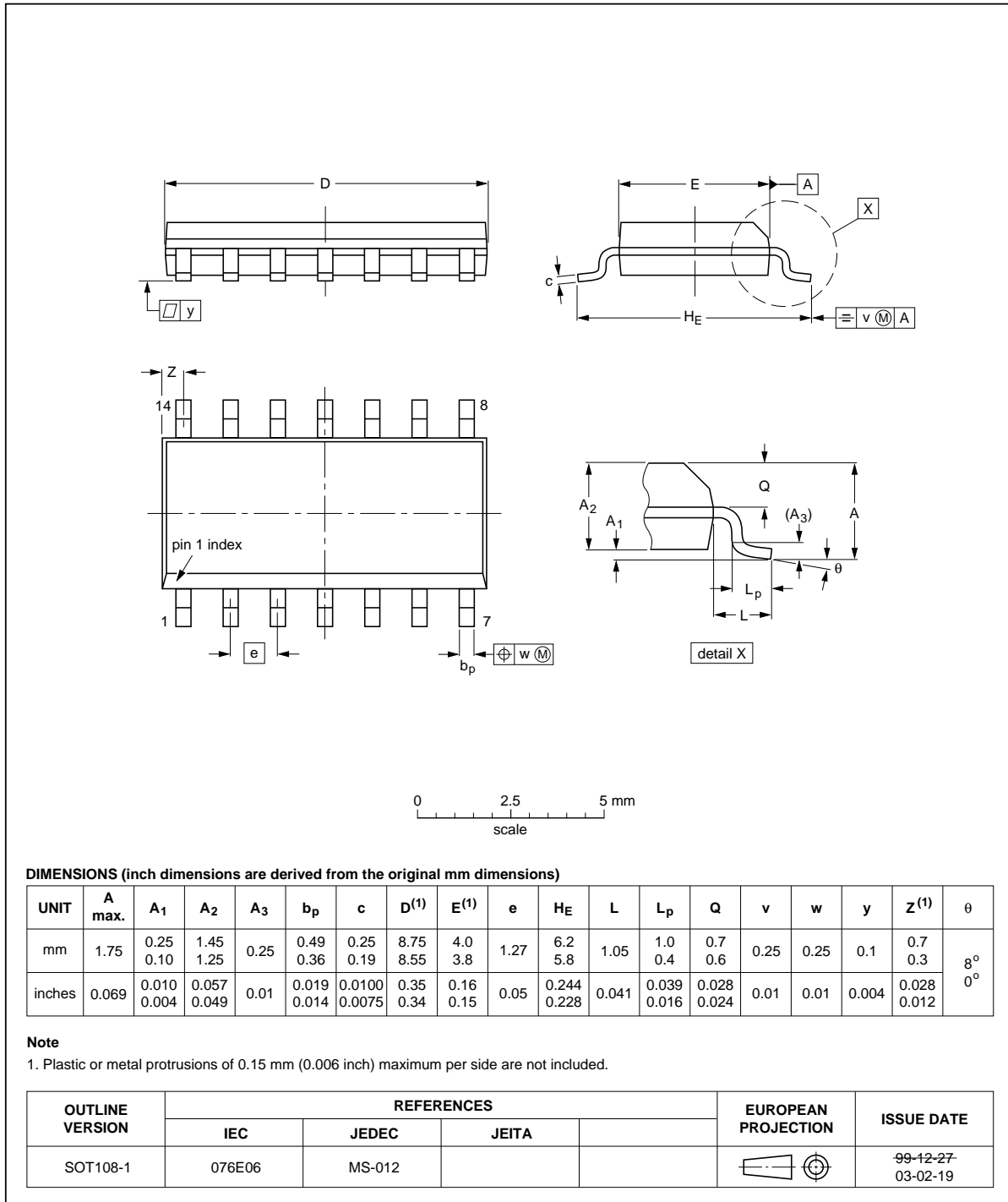


Fig 8. Package outline SOT108-1 (SO14)

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1

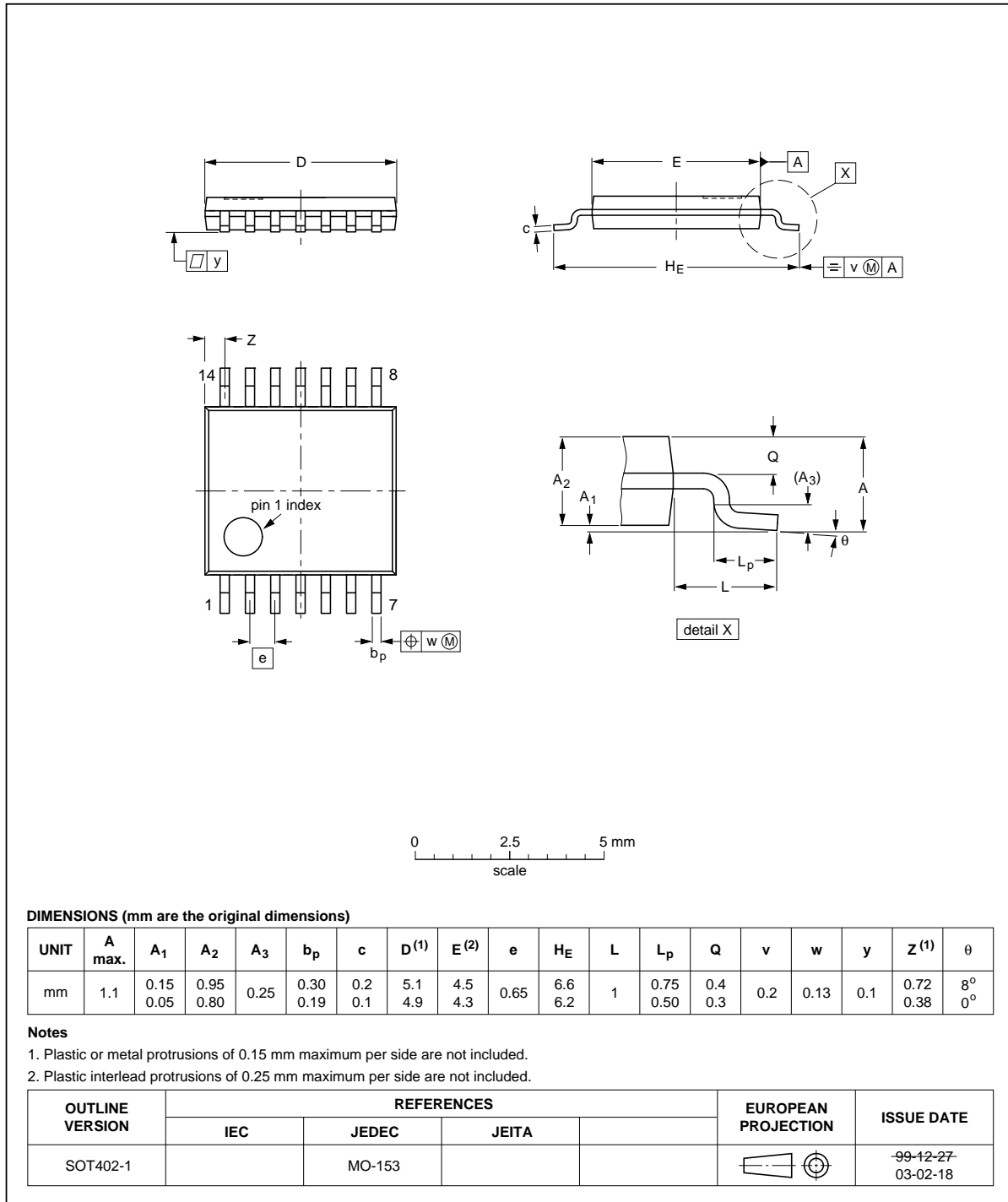


Fig 9. Package outline SOT402-1 (TSSOP14)

DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm **SOT762-1**

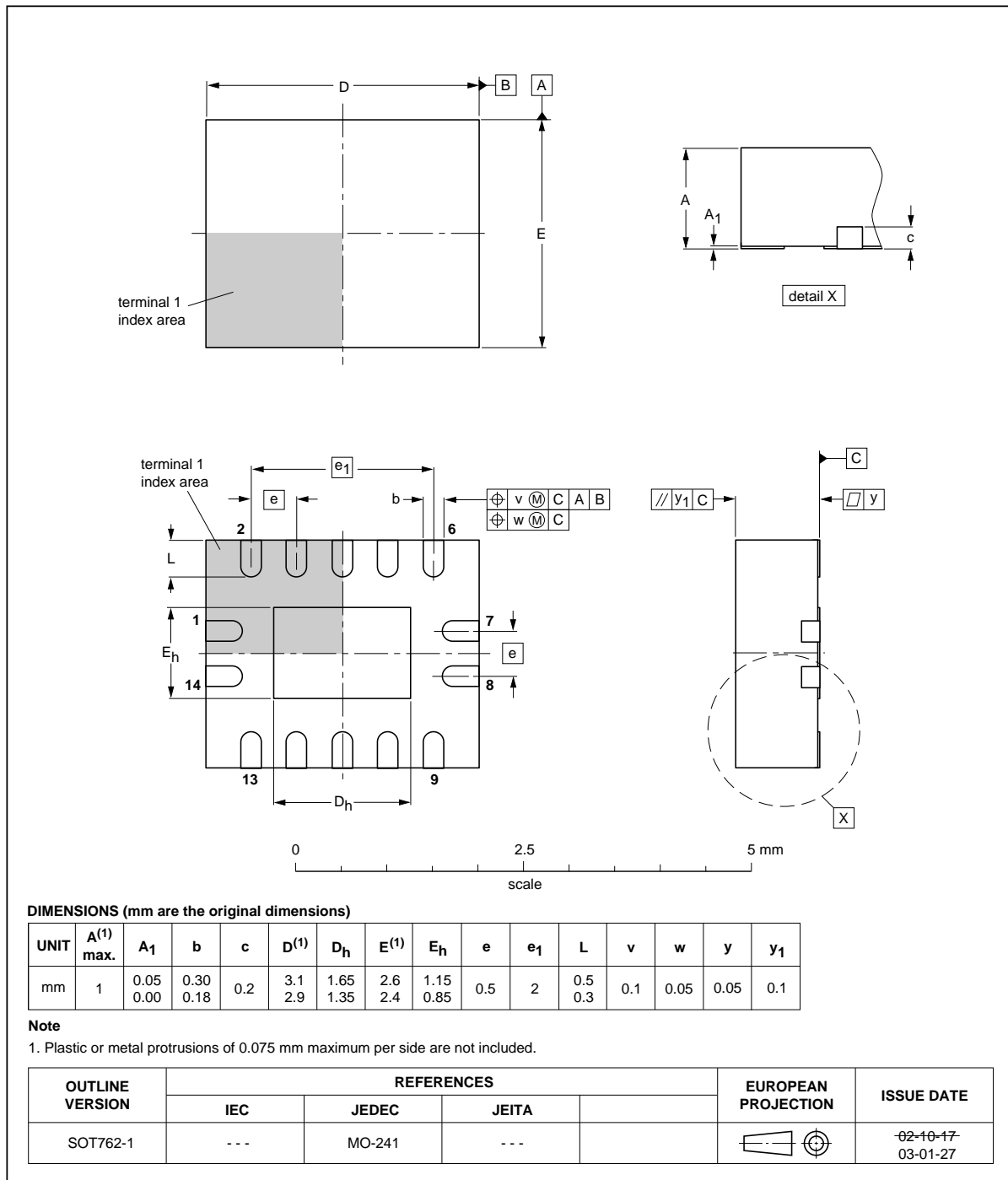


Fig 10. Package outline SOT762-1 (DHVQFN14)

13. Abbreviations

Table 10. Abbreviations

| Acronym | Description |
|---------|--|
| CMOS | Complementary Metal-Oxide Semiconductor |
| DUT | Device Under Test |
| ESD | ElectroStatic Discharge |
| HBM | Human Body Model |
| LSTTL | Low-power Schottky Transistor-Transistor Logic |
| MM | Machine Model |
| TTL | Transistor-Transistor Logic |
| MIL | Military |

14. Revision history

Table 11. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|---------------------|--------------|--------------------|---------------|------------|
| 74HC_HCT00_Q100 v.1 | 20120712 | Product data sheet | - | - |

15. Legal information

15.1 Data sheet status

| Document status ^{[1][2]} | Product status ^[3] | Definition |
|-----------------------------------|-------------------------------|---|
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